

Mitigating the effect of R.H.P. Zero

Method -1: Nulling Resistor.

$$\rightarrow R_c > \frac{1}{g_{m2}}$$

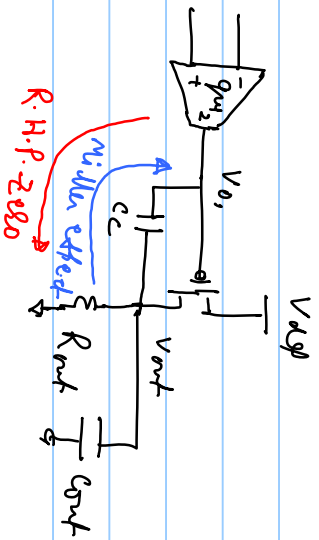
R.H.P. will go away or convert to L.H.P.

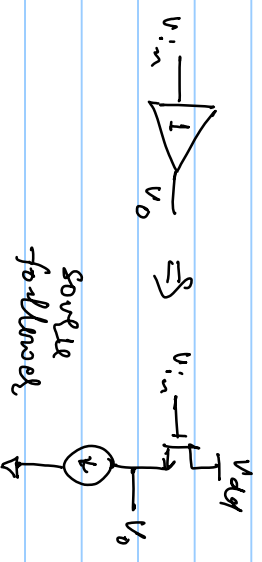
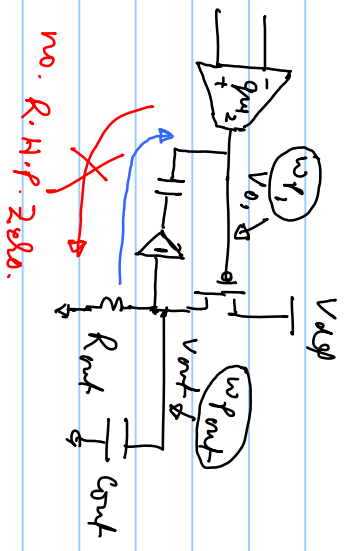
Method -2

choose $g_{m3} \gg g_{m2}$

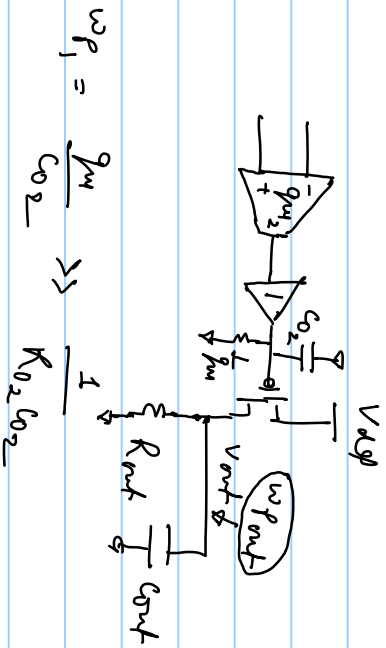
So R.H.P. is pushed at high freq. and phase margin is not affected.

Method -3

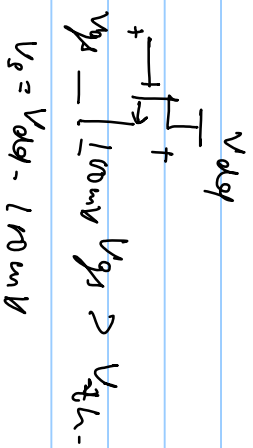




Reducing the effect of ω_p , if ω_{out} is dominant



Reducing the gate capacitor.



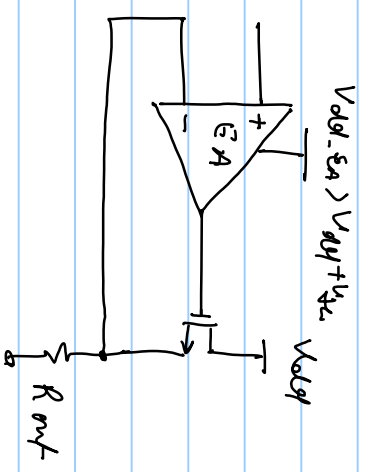
$V_s = V_{d1} - 100 \text{ mV}$

if $V_{drop} = 100 \text{ mV}$

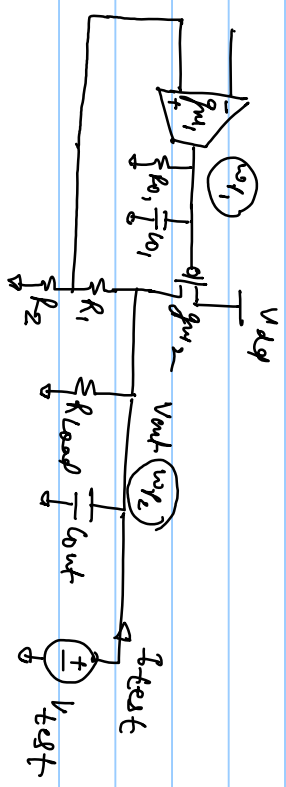
$$V_g > V_{th} + V_{dd} - 100 \text{ mV}$$

$$V_{th} \approx 500 \text{ mV}$$

$$V_g > V_{dd} + 400 \text{ mV}$$



Output Impedance of CMOS LDD



$$R_{out} = (R_1 + R_2) \parallel R_{O2} \parallel R_{Load}$$

$$Z_{out} = \frac{V_{test}}{I_{test}}$$

all e output impedance.

$$Z_{out}(d.c) = \frac{R_{out}}{1 + \beta A_0}$$

$$A_0 = g_{m1} R_{O1} \times g_{m2} R_{out}$$

$$\begin{aligned} Z_{out} &= \frac{R_{out} / (1 + R_{out} / \text{units})}{1 + \beta A_0} = \frac{R_{out}}{(1 + \beta / w_{p2}) \left(\frac{1 + \beta A_0}{(1 + \beta / w_{p1}) (1 + \beta / w_{p2})} \right)} \\ &= \frac{R_{out}}{(1 + \beta / w_{p2}) \left(\frac{1 + \beta / w_{p1}}{(1 + \beta / w_{p1}) (1 + \beta / w_{p2})} + \beta A_0 \right)} \end{aligned}$$

$$= \frac{R_{out} (1 + s/w_{p1})}{(1 + s/w_{p1})(1 + s/w_{p2}) + \beta A_0}$$

for $w \ll w_{p1}$

$$Z_{out} = \frac{R_{out} (1 + s/w_{p1})}{1 + s/w_{p1} + \beta A_0} = \left(\frac{R_{out}}{1 + \beta A_0} \right) \frac{(1 + s/w_{p1})}{1 + s/(1 + \beta A_0)w_{p1}}$$

